IN THE SPECIFICATION

Please enter the following amendments to the specification.

The paragraph at p. 9, line 14:

In an ensuing step, a second bottom electrode 230B is formed upon the top face of the first bottom electrode 230A, thereby forming a composite bottom electrode 230 of Ir/Pt. Herein, the second bottom electrode 230A can be a single layer or multi-layers by using a material selected from the group consisting of platinum (Pt), iridium (Ir), iridium oxide (IrO_X), ruthenium (Ru), rhenium (Re), rhodium (Rh), tungsten (W), titanium (Ti) and a combination thereof.

The paragraph at p. 9, line 22:

Subsequently, referring to Fig. 2D, exposed surfaces of the composite bottom electrode 230 are oxidized through an oxidation process, thereby forming a conductive oxide 240 of IrO_X on sidewalls of the first bottom electrode 230A. The oxidation process is carried out by using plasma gas selected from the group consisting of oxygen (O_2) gas, argon (Ar) gas, nitrogen (N_2) gas, chlorine (Cl) gas, fluorine (F) gas and a combination thereof, at a temperature ranging from a room temperature to about 400° C. At this time, DC or RF voltage can be applied to the oxidation process. Alternatively, the oxidation process can be carried out through an annealing process in an ambient of O_2 gas, N_2 gas or a mixture gas of O_2 and N_2 at a temperature ranging from about 200° C to about 600° C.

The paragraph at p. 10, line 9:

In a next step, referring to Fig. 2E, a dielectric layer 234 is formed on exposed surfaces of the composite bottom electrode 230 and the third ILD 232 using a method such as a spin coating technique or the like, wherein the dielectric layer ~~232~~ 234 employs

a ferroelectric material with a perovskite structure or a layered perovskite structure such as strontium bismuth tantalate ($SrBi_2Ta_2O_9$, hereinafter referred to as SBT), lanthanum (La)-modified bismuth titanate ($(Bi,La)_4Ti_3O_{12}$, hereinafter referred to as BLT), lead zirconium titanate ($(Pb,Zr)TiO_3$, hereinafter referred to as PZT) ~~),~~, neodymium (Nd)-modified bismuth titanate ($(Bi,Nd)_4Ti_3O_{12}$, hereinafter referred to as BNdT), vanadium (V)-modified bismuth titanate ($(Bi,V)_4Ti_3O_{12}$, hereinafter referred to as BVT) or the like. In utilizing the ferroelectric material, the ferroelectric material doped with impurities can be used for the dielectric layer 234.

The paragraph at p. 10, line 25:

Finally, a top electrode 236 is formed upon the dielectric layer 234, which is situated above the composite bottom electrode 230, as depicted in Fig. 2E. The top electrode 236 can be a single layer or multi-layers by employing a material selected from the group consisting of Pt, Ir, IrO_X, Ru, Re, Rh, W, Ti and a combination thereof. After a formation of the top electrode 236, an annealing process is carried out for recovering a ferroelectric property of the FeRAM capacitor. Thus, the inventive process for manufacturing the FeRAM capacitor is completed.

The paragraph at p. 11, line 9:

In comparison with the prior art method, the exposed sidewalls of the first bottom electrode 230A of Ir are oxidized through the plasma process or the annealing process before a formation of the dielectric layer 234, whereby the conductive oxide 240 of IrO_X is formed on the exposed sidewalls of the first bottom electrode 230A. While Ir has a poor adhesive property with respect to the dielectric layer 234, IrO_X has a good adhesive property. Therefore, a delaminating phenomenon introduced between the exposed sidewalls of the first bottom electrode 230A and the dielectric layer 234, which is a serious problem in the prior art, can be effectively prevented in accordance with the present invention owing to the conductive oxides 240 of IrO_X. Furthermore, micro-voids in the dielectric layer 234 which is introduced due to the delaminating phenomenon can

be also removed with effect, whereby it is possible to obtain a reliable and an enhanced FeRAM capacitor.